



*) J·B!7 \UbbY·ACG:9Hg· @87* -+(L!)

PPAK5X6 Pin Configuration

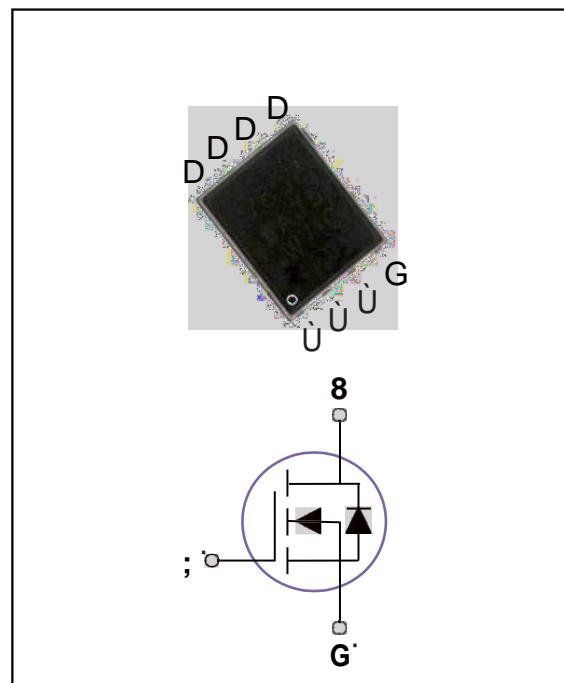
BVDSS	RDS(on)	ID
65V	Gei {	100A

Features

- Improved dv/dt capability
- Fast switching
- 100% EAS available
- Available

Applications

- Networking
- Load Switch
- LED applications
- Charger



A 5L=A I A F 5H=B ; G 5B8 7<5F57H9F=GH=7G

@ 25°C Ambient Temperature (unless otherwise noted)

DUFUaYhYf Qq=<DU '•Kq%,>q=<D5 U. ; € ÄB• ' U. ±È \D Rau[r±È \DIU U. TM±È \DU 'u[q%,> € ÄCgTB...G @ 7

	* 6	Z20/-12	V
Drain Current – Continuous (T _c =257)	I _D	100	A
Drain Current – Continuous (T _c =1007)		63	A
Drain Current – Pulsed ¹	I _{DM}	400	A
Single Pulse Avalanche Energy ²	EAS	245	mJ
Single Pulse Avalanche Current ²	I _{AS}	70	A
Power Dissipation (T _c		2 W	
Power Dissipation – Derate above 257		1.14	W/7
Storage Temperature Range	T _{STG}	-50 to 150	-50 to 150 °C
Operating Junction Temperature T _j	s		

Thermal Resistance Junction to ambient	R _{RAE}	---	62	°C/W
Thermal Resistance Junction to Case	R _{RC}	---	0.88	°C/W

ACG:9H'9@97HF=75@'7<5F57H9F=GH=7G' $T_A=25$ "unless otherwise specified

DUFUa YhYf'

Gma Vc`'

7cbXjh]cbg'

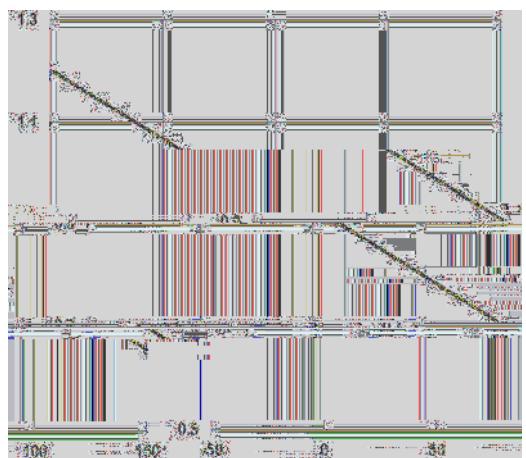
A]b"

Hmd"

AU1"

I b]h'



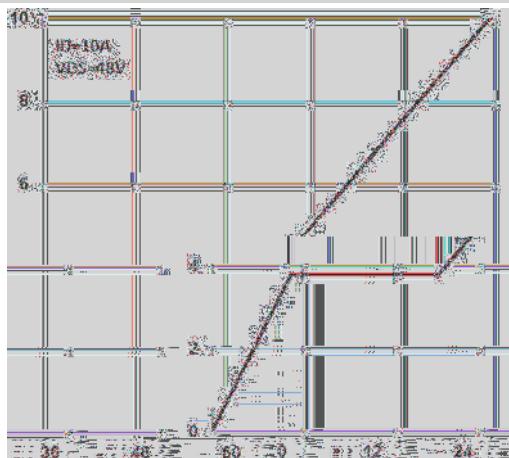


T_J , Junction Temperature

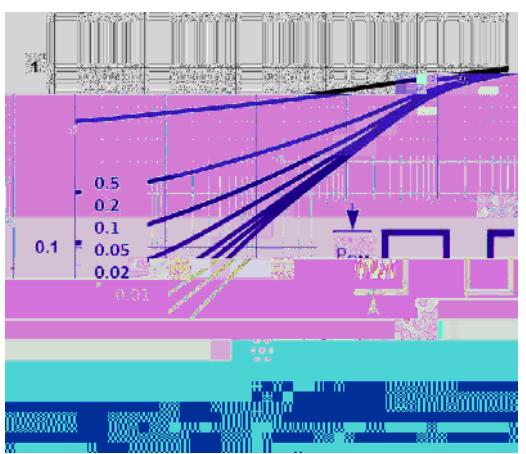
(7) Fig.3 Normalized V_{th} vs. T_J

T_J , Junction Temperature

(7) Fig.2 Normalized RDSON vs.
 T_J

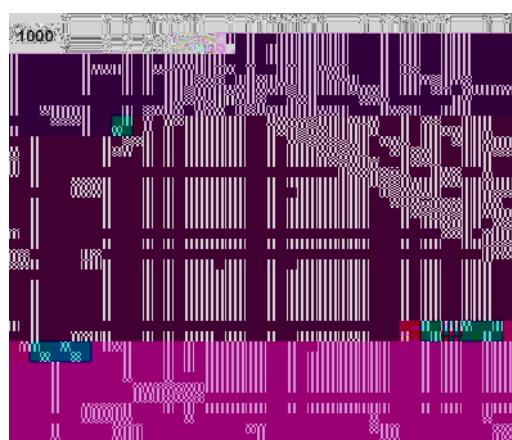


Q_g , Gate Charge (nC)



Square Wave Pulse Duration (s)

Fig.5 Normalized Transient Impedance



V_{DS} , Drain to Source Voltage (V)

Fig.6 Maximum Safe Operation Area
